



安徽富信半导体科技有限公司

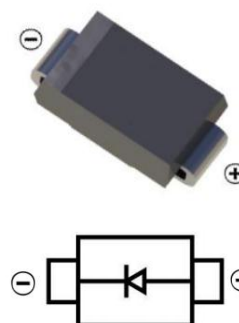
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

GS1Y-GS1Z

SMA General Purpose High Voltage Rectifier Diode 通用高压整流二极管

■Features 特点

Low reverse leakage current 低反向漏电流
High surge current capability 高浪涌电流能力
Built-in strain relief 内应力释放
Surface mount device 表面贴装器件
Case 封装:SMA



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	GS1Y	GS1Z	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	1600	2000	V
DC Reverse Voltage 直流反向电压	V_R	1600	2000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	1120	1400	V
Forward Rectified Current 正向整流电流	I_F	1.5		A
Peak Surge Current 峰值浪涌电流	I_{FSM}	30		A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	95		$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	$150^{\circ}\text{C}, -55^{\circ}\text{C to } 150^{\circ}\text{C}$		

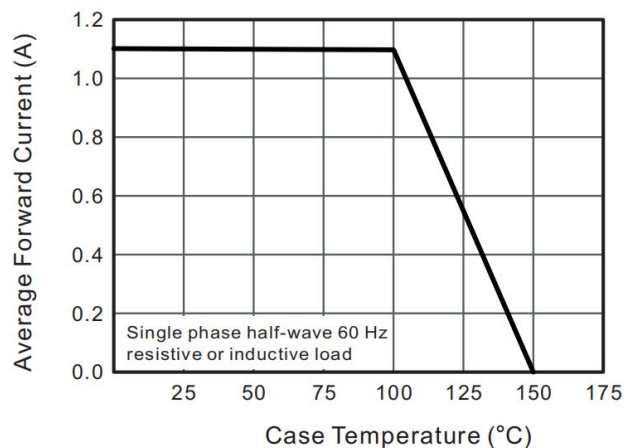
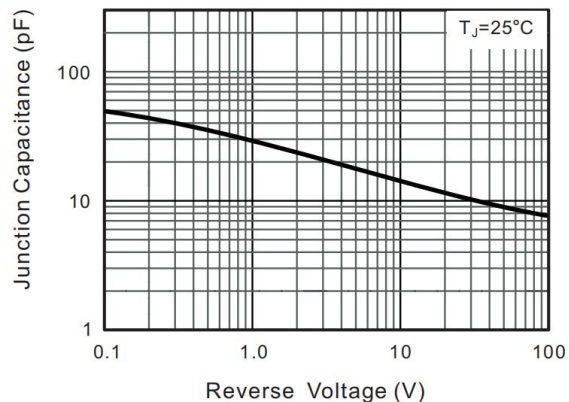
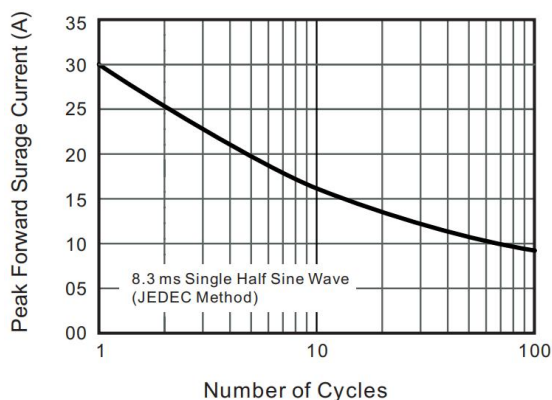
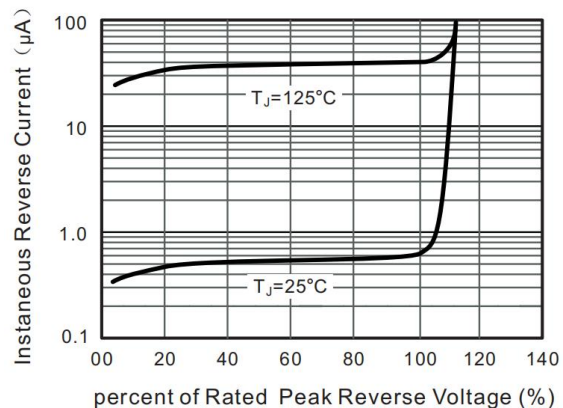
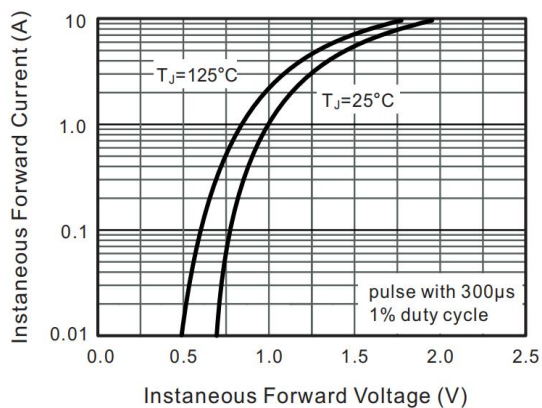
■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Test Condition 测试条件
Forward Voltage 正向电压	V_F			1.15	V	$I_F=1.5\text{A}$
Reverse Current($T_A=25^{\circ}\text{C}/$) 反向电流($T_A=125^{\circ}\text{C}/$)	I_R			5 50	μA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D		20		pF	$V_R=4\text{V}, f=1\text{MHz}$



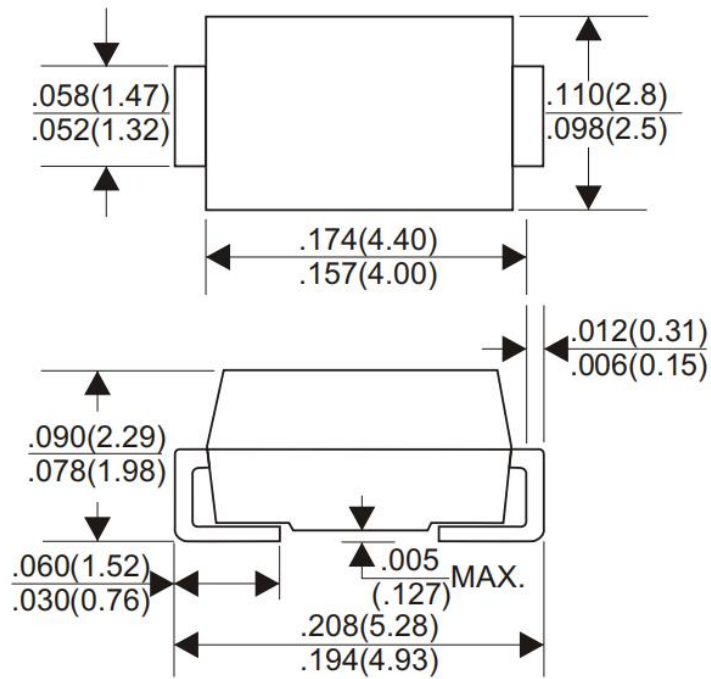
■ Typical Characteristic Curve 典型特性曲线





■Dimension 外形封装尺寸

DO-214AC(SMA)



Dimensions in inches and (millimeters)